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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Benjamin A. Haskell et al. Examiner: To be assigned
Serial No.: 10/537,385 ✓ Group Art Unit: 2811
Filed: June 3, 2005 Docket: G&C 30794.94-US-WO
Title: GROWTH OF PLANAR, NON-POLAR A-PLANE GALLIUM NITRIDE BY HYDRIDE
VAPOR PHASE EPITAXY

CERTIFICATE OF MAILING UNDER 37 CFR 1.10

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By: *Barbara Senty*

Name: Barbara Senty

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Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Dear Sir:

We are transmitting herewith the attached:

- ☒ Transmittal sheet, in duplicate, containing a Certificate of Mailing under 37 CFR 1.10.
- ☒ Information Disclosure Statement and Form PTO-1449.
- ☒ Cited Reference(s).
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GATES & COOPER LLP

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By: *George H. Gates*

Name: George H. Gates

Reg. No.: 33,500

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INFORMATION DISCLOSURE STATEMENT(37 C.F.R. §1.97(b))

MAIL STOP AMENDMENT

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

This statement should be considered because it is submitted before the mailing date of a first Office Action on-the-merits. Accordingly, no fee is due for consideration of the items listed on the enclosed Form 1449.

In accordance with 37 C.F.R. §1.98(a)(2), a copy of each foreign patent document and each non-patent document listed on the enclosed Form 1449 is provided.

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§ 102 and 103 and Applicants reserve the right, pursuant to 37 C.F.R. § 1.131 or otherwise, to establish that

the reference(s) are not "prior art". Moreover, Applicants do not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended.

Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Please direct any response or inquiry to the below-signed attorney at (310) 641-8797.

Respectfully submitted,

GATES & COOPER LLP
Attorneys for Applicant(s)

Howard Hughes Center
6701 Center Drive West, Suite 1050
Los Angeles, California 90045
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Date: April 20, 2006

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By: 

George H. Gates
Reg. No.: 33,500

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